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11-22-02
Muller

THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of

John W. ANDREWS et al.

Serial No.: 09/883,981

Group Art Unit: 2813

Filed: June 20, 2001

Examiner: David S. Blum

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TECHNOLOGY CENTER 2800

For: LOW COST SHALLOW TRENCH ISOLATION USING NON-CONFORMAL
DIELECTRIC MATERIAL

Honorable Commissioner of Patents
Washington, D.C. 20231

AMENDMENT UNDER 37 C.F.R. §1.111

Sir:

In response to the Office Action dated August 20, 2002, please amend the above-identified application as follows:

IN THE CLAIMS:

Please amend the claims to read as follows:

SUB F1
E1

8. (Thrice Amended) A semiconductor substrate comprising:
a trench region comprising at least one trench, said trench comprising a single layer of non-nitrided seamless filler material having an unpolished upper surface; and
a non-trench region having an upper surface which is substantially co-planar with said unpolished upper surface of said single layer of said non-nitrided seamless filler material.

SUB F2
E2

15. (Thrice Amended) A semiconductor substrate comprising:
a trench region comprising at least one trench, said trench comprising a single layer of non-nitrided seamless high density plasma (HDP) oxide having an unpolished upper surface;
and
a non-trench region having an upper surface which is substantially co-planar with said unpolished upper surface of said single layer of said non-nitrided seamless HDP oxide.

SUB F3
E3

23. (Four Times Amended) A semiconductor substrate comprising: